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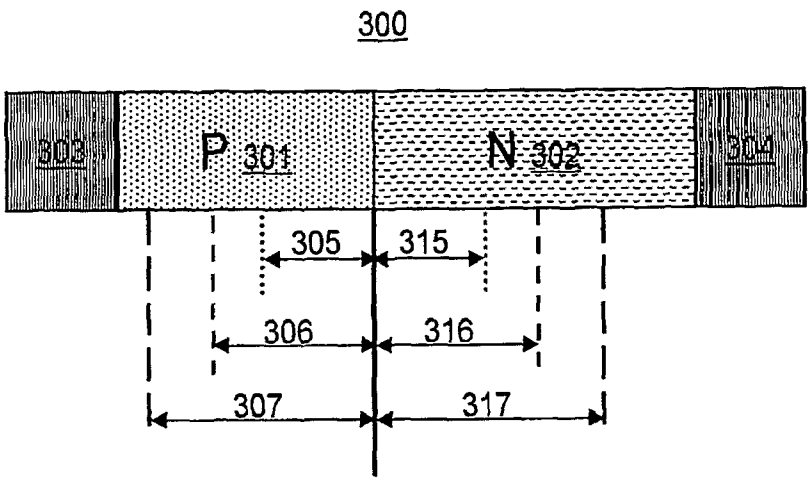
(54) Title: NEAR NATURAL BREAKDOWN DEVICE



(57) Abstract: A semiconductor device includes a semiconductor region wherein the semiconductor region is a forced or non-forced Near Natural breakdown region, which is completely depleted when a predetermined voltage having a magnitude less than or equal to the breakdown voltage of a non-Natural breakdown (for example, Zener breakdown and Avalanche breakdown) is applied across the device.

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